NPN Epitaxial Silicon Transistor

KSC2383

ABSOLUTE MAXIMUM RATINGS

(Values are at T_A = 25°C unless otherwise noted.)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	160	V
V _{CEO}	Collector-Emitter Voltage	160	V
V _{EBO}	Emitter-Base Voltage	6	V
I _C	Collector Current	1	Α
Ι _Β	Base Current	0.5	Α
T_J	Junction Temperature	150	°C
T _{STG}	Storage Temperature	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

(Values are at $T_A = 25^{\circ}C$ unless otherwise noted.) (Note 1)

Symbol	Parameter	Value	Unit
P _D	Power Dissipation	900	mW
	Derate Above 25°C	7.2	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	138	°C/W

1. PCB size: FR-4, 76 mm \times 114 mm \times 1.57 mm (3.0 inch \times 4.5 inch \times 0.062 inch) with minimum land pattern size.



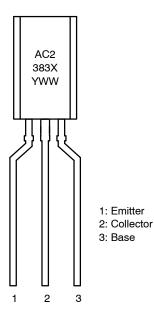
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TO-92 3 LF CASE 135AM

MARKING DIAGRAM



A = Assembly Code C2383 = Device Code X = O / Y YWW = Date Code

ORDERING INFORMATION

Device	Package	Shipping
KSC2383OTA	TO-92 3 LF (Pb-Free)	2000 / Fan–Fold
KSC2383YTA	TO-92 3 LF (Pb-Free)	2000 / Fan–Fold

ELECTRICAL CHARACTERISTICS

(Values are at $T_A = 25^{\circ}C$ unless otherwise noted.)

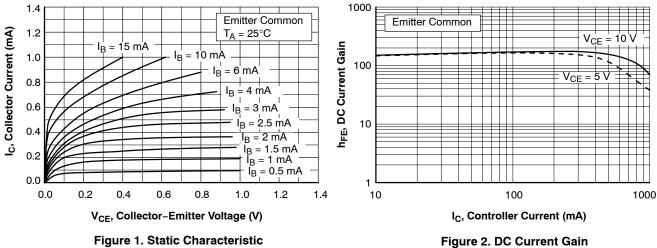
Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
I _{CBO}	Collector Cut-Off Current	V _{CB} = 150 V, I _E = 0	-	-	1	μΑ
I _{EBO}	Emitter Cut-Off Current	V _{EB} = 6 V, I _C = 0	-	-	1	μΑ
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C = 10 mA, I _B = 0	160	-	-	V
h _{FE}	DC Current Gain	V _{CE} = 5 V, I _C = 200 mA	60	-	320	
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C = 500 mA, I _B = 50 mA	-	-	1.5	V
V _{BE} (on)	Base-Emitter On Voltage	$V_{CE} = 5 \text{ V}, I_{C} = 5 \text{ mA}$	0.45	_	0.75	V
f _T	Current Gain Bandwidth Product	V _{CE} = 5 V, I _C = 200 mA	20	100	-	MHz
C _{ob}	Output Capacitance	V _{CB} = 10 V, I _E = 0, f = 1 MHz	-	=	20	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

hFE CLASSIFICATION

Classification	R	0	Υ
h _{FE}	60 ~ 120	100 ~ 200	160 ~ 320

TYPICAL PERFORMANCE CHARACTERISTICS



1000 **Emitter Common Emitter Common** V_{BE}(sat), V_{CE}(sat), Saturation $T_A = 25^{\circ}C$ $T_A = 25^{\circ}C$ h_{FE}, DC Current Gain Voltage (V) $I_{\rm C} / I_{\rm B} = 10$ 100 V_{CE} = 10 V $V_{CE} = 5 V$ 0.01 $V_{CE} = 1 V$ 10 0.001 100 1000 10 100 1000 I_C, Controller Current (mA) I_C, Controller Current (mA)

Figure 3. DC Current Gain

Figure 4. Collector-Emitter Saturation Voltage

KSC2383

TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

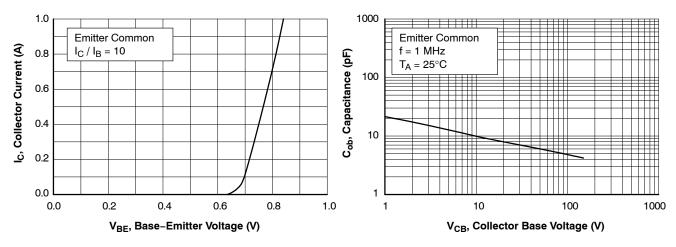


Figure 5. Base-Emitter On Voltage

Figure 6. Collector Output Capacitance

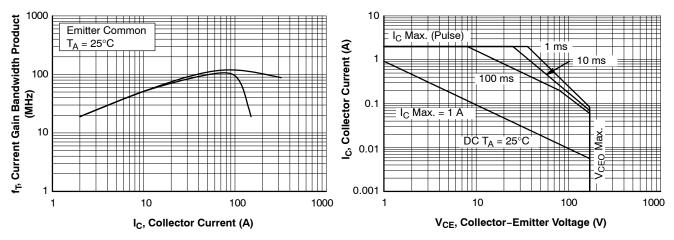
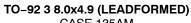


Figure 7. Current Gain Bandwidth Product

Figure 8. Safe Operating Area





CASE 135AM ISSUE B

DATE 14 JAN 2021



- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, GATE REMAINS AND TIE BAR PROTRUSIONS.
- 4. DIMENSION & AND &2 DOES NOT INCLUDE DAMBAR PROTRUSION.
 DIMENSION &2 LOCATED ABOVE THE DAMBAR PORTION OF MIDDLE LEAD.

	MILLIMETERS			
DIM	MIN.	N□M.	MAX.	
Α	3.70	3.90	4.10	
A1	1.25	1.45	1.65	
b	0.35	0.50	0.60	
b2	0.62		0.78	
С	0.35	0.45	0.55	
D	7.80	8.00	8,20	
Ε	4.70	4.70 4.90		
E2	3.70 3.90		4.10	
е	1.27 BSC			
e2	2.50 BSC			
F	2.45 REF			
L	13.00 REF			
L2	1.50		1.90	
L3	2.60		3,40	
L4	10.40 REF			

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END VIEW

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